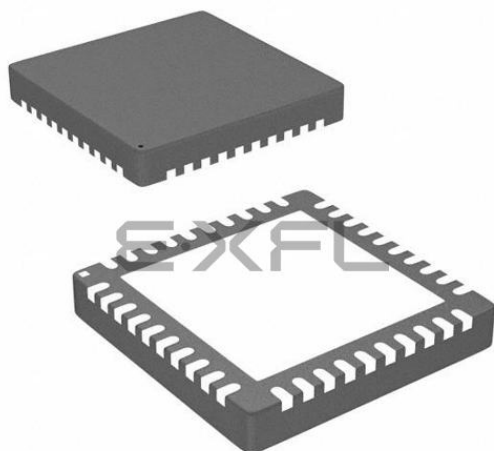




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I ² C, IrDA, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	20
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 6x16b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-QFN-EP (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk20dx128vfm5

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1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to <http://www.freescale.com> and perform a part number search for the following device numbers: PK20 and MK20 .

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q K## A M FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	- M = Fully qualified, general market flow - P = Prequalification
K##	Kinetis family	K20
A	Key attribute	- D = Cortex-M4 w/ DSP - F = Cortex-M4 w/ DSP and FPU
M	Flash memory type	- N = Program flash only - X = Program flash and FlexMemory

Table continues on the next page...

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	130	μA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

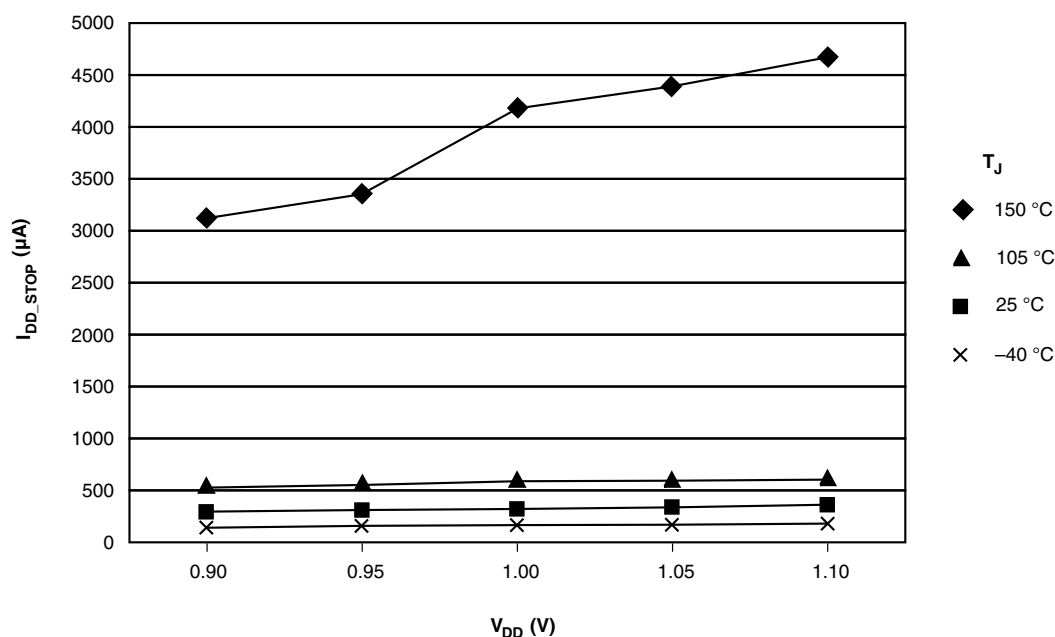
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V_{DD} -to- V_{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V_{SS} -to- V_{SSA} differential voltage	-0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	$0.7 \times V_{DD}$	—	V	
		$0.75 \times V_{DD}$	—	V	
V_{IL}	Input low voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	—	$0.35 \times V_{DD}$	V	
		—	$0.3 \times V_{DD}$	V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICIO}	I/O pin DC injection current — single pin $V_{IN} < V_{SS}-0.3\text{V}$ (Negative current injection) $V_{IN} > V_{DD}+0.3\text{V}$ (Positive current injection)	-3 —	— +3	mA	1
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins - Negative current injection - Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} ($=V_{SS}-0.3\text{V}$) and V_{IN} is less than V_{AIO_MAX} ($=V_{DD}+0.3\text{V}$) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/|I_{IC}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/|I_{IC}|$. Select the larger of these two calculated resistances.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V _{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
V _{LVW1H} V _{LVW2H} V _{LVW3H} V _{LVW4H}	Low-voltage warning thresholds — high range • Level 1 falling (LVWV=00) • Level 2 falling (LVWV=01) • Level 3 falling (LVWV=10) • Level 4 falling (LVWV=11)	2.62 2.72 2.82 2.92	2.70 2.80 2.90 3.00	2.78 2.88 2.98 3.08	V V V V	1
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±80	—	mV	
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
V _{LVW1L} V _{LVW2L} V _{LVW3L} V _{LVW4L}	Low-voltage warning thresholds — low range • Level 1 falling (LVWV=00) • Level 2 falling (LVWV=01) • Level 3 falling (LVWV=10) • Level 4 falling (LVWV=11)	1.74 1.84 1.94 2.04	1.80 1.90 2.00 2.10	1.86 1.96 2.06 2.16	V V V V	1
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±60	—	mV	
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I _{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	867	—	μA	6
I _{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	1.1	—	mA	7
I _{DD_VLPW}	Very-low-power wait mode current at 3.0 V	—	509	—	μA	8
I _{DD_STOP}	Stop mode current at 3.0 V • @ -40 to 25°C • @ 70°C • @ 105°C	—	310	426	μA	
		—	384	458	μA	
		—	629	1100	μA	
I _{DD_VLPS}	Very-low-power stop mode current at 3.0 V • @ -40 to 25°C • @ 70°C • @ 105°C	—	3.5	22.6	μA	
		—	20.7	52.9	μA	
		—	85	220	μA	
I _{DD_LLS}	Low leakage stop mode current at 3.0 V • @ -40 to 25°C • @ 70°C • @ 105°C	—	2.1	3.7	μA	
		—	7.7	43.1	μA	
		—	32.2	68	μA	
I _{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V • @ -40 to 25°C • @ 70°C • @ 105°C	—	1.5	2.9	μA	
		—	4.8	22.5	μA	
		—	20	37.8	μA	
I _{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V • @ -40 to 25°C • @ 70°C • @ 105°C	—	1.4	2.8	μA	
		—	4.1	19.2	μA	
		—	17.3	32.4	μA	
I _{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V • @ -40 to 25°C • @ 70°C • @ 105°C	—	0.678	1.3	μA	
		—	2.8	13.6	μA	
		—	13.6	24.5	μA	
I _{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled • @ -40 to 25°C • @ 70°C • @ 105°C	—	0.367	1.0	μA	
		—	2.4	13.3	μA	
		—	13.2	24.1	μA	

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled • @ -40 to 25°C • @ 70°C • @ 105°C	— — —	0.176 2.2 13	0.859 13.1 23.9	μA μA μA	
I_{DD_VBAT}	Average current with RTC and 32kHz disabled at 3.0 V • @ -40 to 25°C • @ 70°C • @ 105°C	— — —	0.19 0.49 2.2	0.22 0.64 3.2	μA μA μA	
I_{DD_VBAT}	Average current when CPU is not accessing RTC registers • @ 1.8V • @ -40 to 25°C • @ 70°C • @ 105°C • @ 3.0V • @ -40 to 25°C • @ 70°C • @ 105°C	— — — — — — —	0.57 0.90 2.4 0.67 1.0 2.7	0.67 1.2 3.5 0.94 1.4 3.9	μA μA μA μA μA μA	9

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. 50MHz core and system clock, 25MHz bus clock, and 25MHz flash clock. MCG configured for FEI mode. All peripheral clocks disabled.
3. 50MHz core and system clock, 25MHz bus clock, and 25MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled, and peripherals are in active operation.
4. Max values are measured with CPU executing DSP instructions
5. 25MHz core and system clock, 25MHz bus clock, and 12.5MHz flash clock. MCG configured for FEI mode.
6. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
7. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing from flash.
8. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.
9. Includes 32kHz oscillator current and RTC operation.

5.2.5.1 Diagram: Typical I_{DD_RUN} operating behavior

The following data was measured under these conditions:

- MCG in FBE mode
- USB regulator disabled
- No GPIOs toggled

- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL

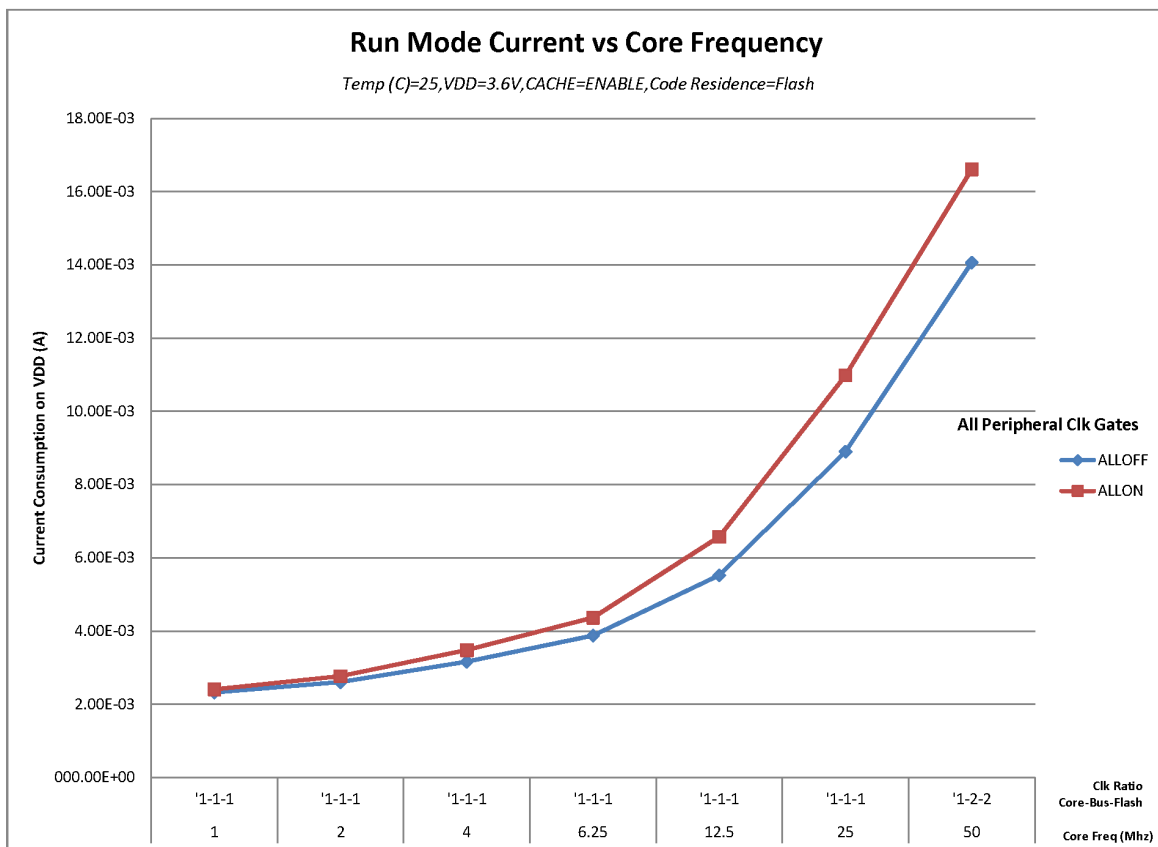


Figure 2. Run mode supply current vs. core frequency

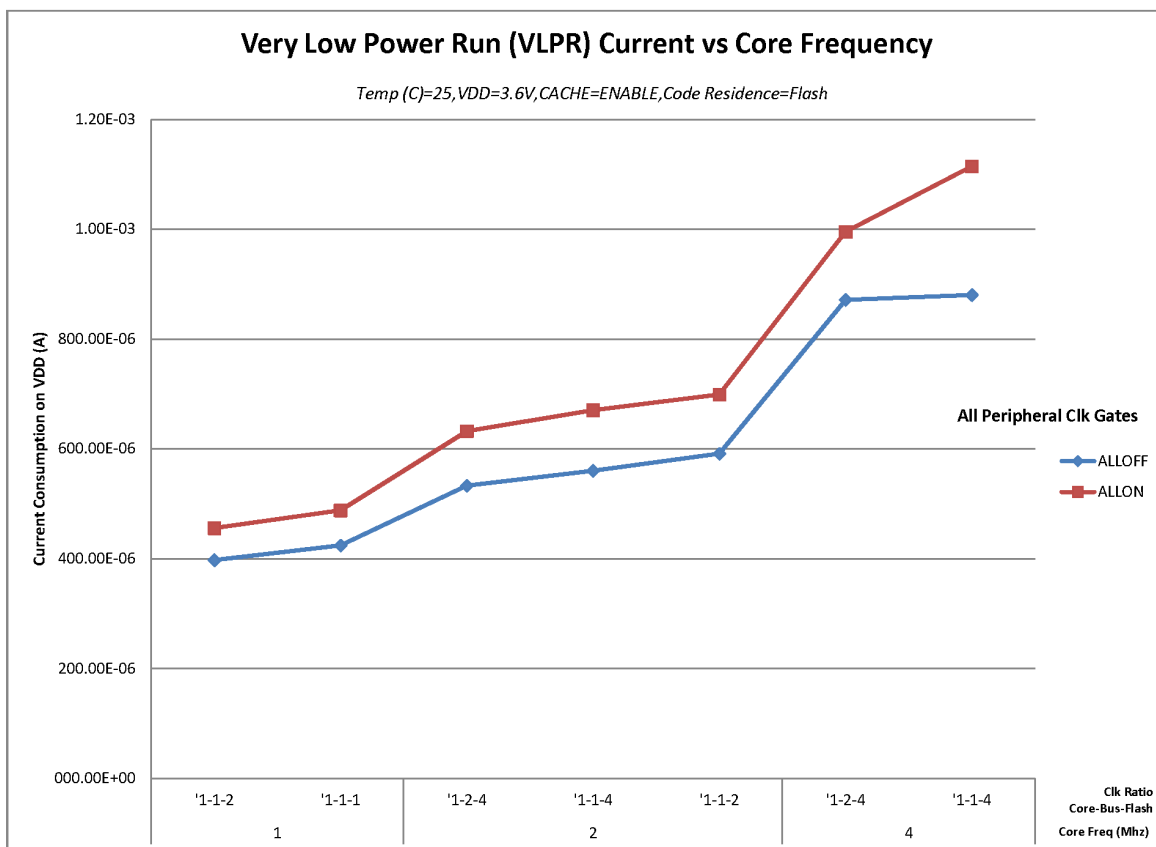


Figure 3. VLPR mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors for 64LQFP

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V _{RE1}	Radiated emissions voltage, band 1	0.15–50	19	dBμV	1, 2
V _{RE2}	Radiated emissions voltage, band 2	50–150	21	dBμV	
V _{RE3}	Radiated emissions voltage, band 3	150–500	19	dBμV	
V _{RE4}	Radiated emissions voltage, band 4	500–1000	11	dBμV	
V _{RE_IEC}	IEC level	0.15–1000	L	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported

Peripheral operating requirements and behaviors

Board type	Symbol	Description	32 QFN	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	78	°C/W	1,3
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	27	°C/W	,
—	$R_{\theta JB}$	Thermal resistance, junction to board	12	°C/W	5
—	$R_{\theta JC}$	Thermal resistance, junction to case	1.5	°C/W	6
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	6	°C/W	7

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)* with the single layer board horizontal. For the LQFP, the board meets the JESD51-3 specification. For the MAPBGA, the board meets the JESD51-9 specification.
3. Determined according to JEDEC Standard JESD51-6, *Integrated Circuits Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)* with the board horizontal.
5. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*. Board temperature is measured on the top surface of the board near the package.
6. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
7. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 JTAG electricals

Table 12. JTAG voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	5.5	V

Table continues on the next page...

Table 13. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
f _{fill_ref}	FLL reference frequency range		31.25	—	39.0625	kHz	
f _{dco}	DCO output frequency range	Low range (DRS=00) 640 × f _{fill_ref}	20	20.97	25	MHz	2, 3
		Mid range (DRS=01) 1280 × f _{fill_ref}	40	41.94	50	MHz	
		Mid-high range (DRS=10) 1920 × f _{fill_ref}	60	62.91	75	MHz	
		High range (DRS=11) 2560 × f _{fill_ref}	80	83.89	100	MHz	
f _{dco_t_DMx3} 2	DCO output frequency	Low range (DRS=00) 732 × f _{fill_ref}	—	23.99	—	MHz	4, 5
		Mid range (DRS=01) 1464 × f _{fill_ref}	—	47.97	—	MHz	
		Mid-high range (DRS=10) 2197 × f _{fill_ref}	—	71.99	—	MHz	
		High range (DRS=11) 2929 × f _{fill_ref}	—	95.98	—	MHz	
J _{cyc_fill}	FLL period jitter		—	180	—	ps	
	• f _{VCO} = 48 MHz • f _{VCO} = 98 MHz		—	150	—		
t _{fill_acquire}	FLL target frequency acquisition time		—	—	1	ms	6
PLL							
f _{vco}	VCO operating frequency		48.0	—	100	MHz	
I _{pll}	PLL operating current • PLL @ 96 MHz (f _{osc_hi_1} = 8 MHz, f _{pll_ref} = 2 MHz, VDIV multiplier = 48)		—	1060	—	μA	7
I _{pll}	PLL operating current • PLL @ 48 MHz (f _{osc_hi_1} = 8 MHz, f _{pll_ref} = 2 MHz, VDIV multiplier = 24)		—	600	—	μA	7
f _{pll_ref}	PLL reference frequency range		2.0	—	4.0	MHz	
J _{cyc_pll}	PLL period jitter (RMS)						8
	• f _{vco} = 48 MHz • f _{vco} = 100 MHz		— —	120 50	— —	ps ps	

Table continues on the next page...

Table 19. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
Word-write to FlexRAM for EEPROM operation						
$t_{\text{eewr16bers}}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
$t_{\text{eewr16b8k}}$	Word-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
$t_{\text{eewr16b16k}}$	• 16 KB EEPROM backup	—	385	1800	μs	
$t_{\text{eewr16b32k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
Longword-write to FlexRAM for EEPROM operation						
$t_{\text{eewr32bers}}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
$t_{\text{eewr32b8k}}$	Longword-write to FlexRAM execution time: • 8 KB EEPROM backup	—	545	1950	μs	
$t_{\text{eewr32b16k}}$	• 16 KB EEPROM backup	—	630	2050	μs	
$t_{\text{eewr32b32k}}$	• 32 KB EEPROM backup	—	810	2250	μs	

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

6.4.1.3 Flash high voltage current behaviors

Table 20. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
$I_{\text{DD_PGM}}$	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
$I_{\text{DD_ERS}}$	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

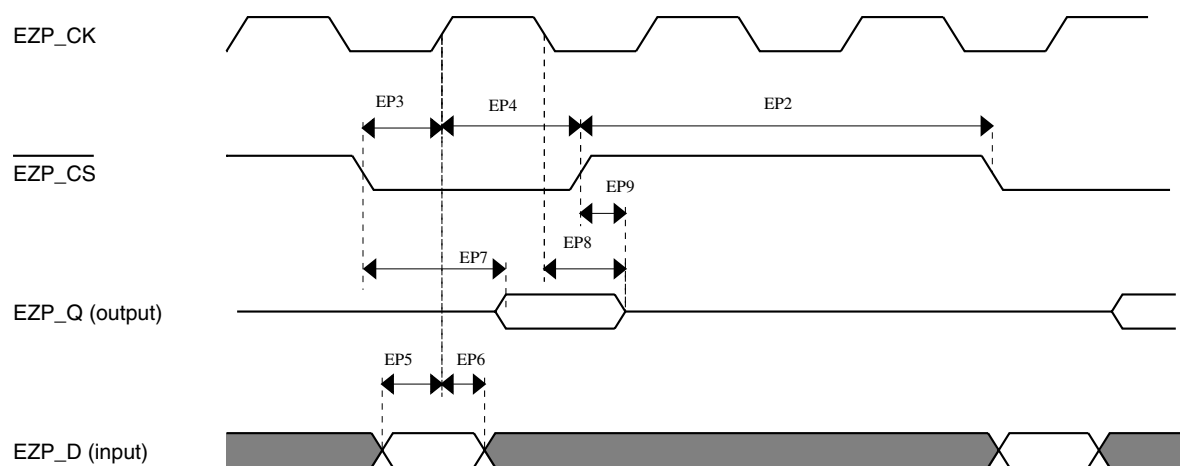
Table 21. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
$t_{\text{nvmretp10k}}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{\text{nvmretp1k}}$	Data retention after up to 1 K cycles	20	100	—	years	
n_{nvmcycp}	Cycling endurance	10 K	50 K	—	cycles	2
Data Flash						
$t_{\text{nvmretd10k}}$	Data retention after up to 10 K cycles	5	50	—	years	

Table continues on the next page...

Table 22. EzPort switching specifications (continued)

Num	Description	Min.	Max.	Unit
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{\text{SYS}}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{\text{SYS}}/8$	MHz
EP2	$\overline{\text{EZP_CS}}$ negation to next $\overline{\text{EZP_CS}}$ assertion	$2 \times t_{\text{EZP_CK}}$	—	ns
EP3	$\overline{\text{EZP_CS}}$ input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to $\overline{\text{EZP_CS}}$ input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—	17	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	$\overline{\text{EZP_CS}}$ negation to EZP_Q tri-state	—	12	ns

**Figure 9. EzPort Timing Diagram**

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

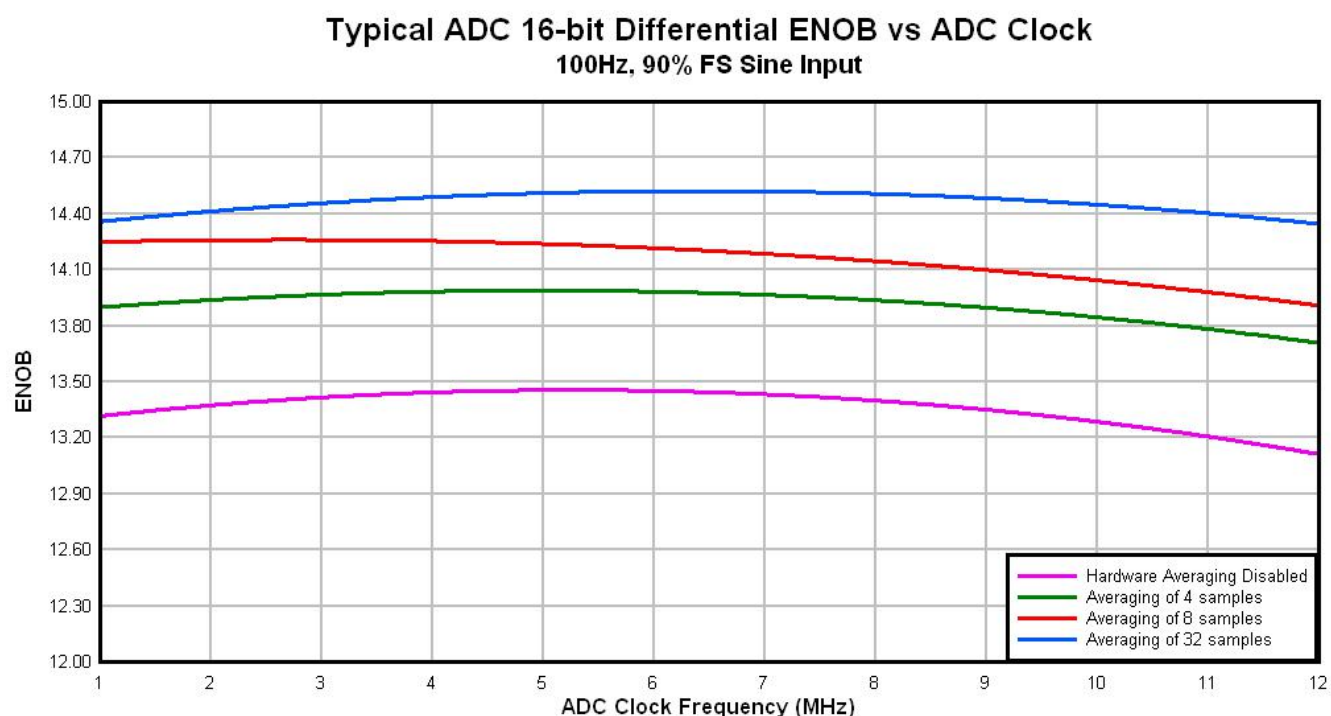


Figure 11. Typical ENOB vs. ADC_CLK for 16-bit differential mode

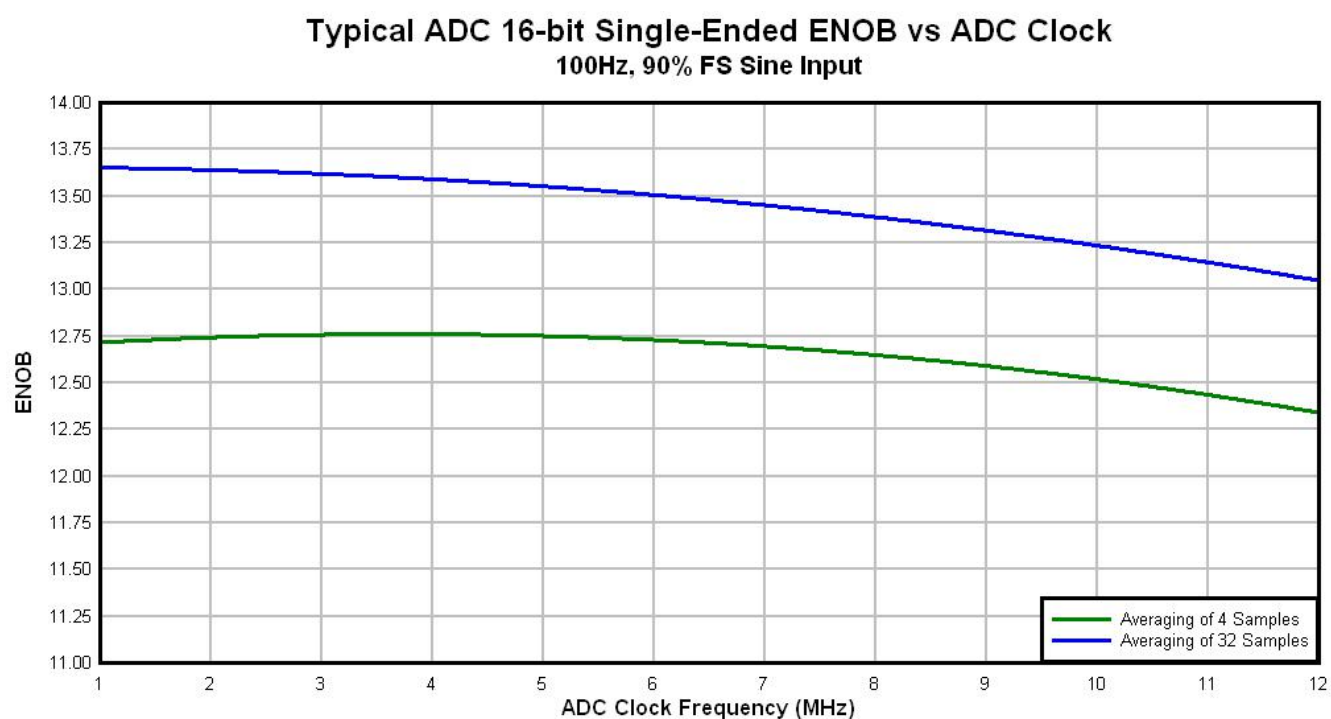


Figure 12. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.8.2 USB DCD electrical specifications

Table 26. USB DCD electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V _{DP_SRC}	USB_DP source voltage (up to 250 μ A)	0.5	—	0.7	V
V _{LGC}	Threshold voltage for logic high	0.8	—	2.0	V
I _{DP_SRC}	USB_DP source current	7	10	13	μ A
I _{DM_SINK}	USB_DM sink current	50	100	150	μ A
R _{DM_DWN}	D- pulldown resistance for data pin contact detect	14.25	—	24.8	k Ω
V _{DAT_REF}	Data detect voltage	0.25	0.33	0.4	V

6.8.3 USB VREG electrical specifications

Table 27. USB VREG electrical specifications

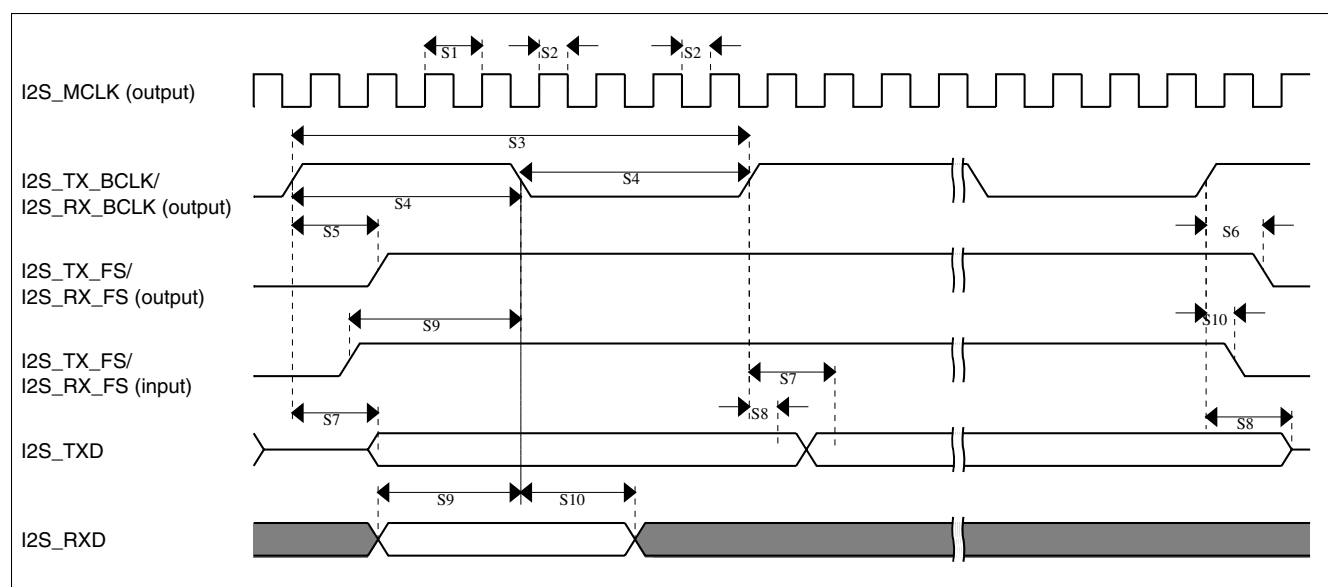
Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
V _{REGIN}	Input supply voltage	2.7	—	5.5	V	
I _{DDon}	Quiescent current — Run mode, load current equal zero, input supply (V _{REGIN}) > 3.6 V	—	120	186	μ A	
I _{DDstby}	Quiescent current — Standby mode, load current equal zero	—	1.1	1.54	μ A	
I _{DDoff}	Quiescent current — Shutdown mode - V_{REGIN} = 5.0 V and temperature=25C - Across operating voltage and temperature	—	650	—	nA	
		—	—	4	μ A	
I _{LOADrun}	Maximum load current — Run mode	—	—	120	mA	
I _{LOADstby}	Maximum load current — Standby mode	—	—	1	mA	
V _{Reg33out}	Regulator output voltage — Input supply (V _{REGIN}) > 3.6 V - Run mode - Standby mode	3	3.3	3.6	V	
		2.1	2.8	3.6	V	
V _{Reg33out}	Regulator output voltage — Input supply (V _{REGIN}) < 3.6 V, pass-through mode	2.1	—	3.6	V	2
C _{OUT}	External output capacitor	1.76	2.2	8.16	μ F	
ESR	External output capacitor equivalent series resistance	1	—	100	m Ω	
I _{LIM}	Short circuit current	—	290	—	mA	

1. Typical values assume V_{REGIN} = 5.0 V, Temp = 25 °C unless otherwise stated.

2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

Table 34. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	62.5	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	250	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	45	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	45	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	45	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

**Figure 21. I2S/SAI timing — master modes****Table 35. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)**

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns

Table continues on the next page...

Table 36. TSI electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f _{REFmax}	Reference oscillator frequency	—	8	15	MHz	2, 3
f _{ELEmax}	Electrode oscillator frequency	—	1	1.8	MHz	2, 4
C _{REF}	Internal reference capacitor	—	1	—	pF	
V _{DELTA}	Oscillator delta voltage	—	500	—	mV	2, 5
I _{REF}	Reference oscillator current source base current • 2 µA setting (REFCHRG = 0) • 32 µA setting (REFCHRG = 15)	— —	2 36	3 50	µA	2, 6
I _{ELE}	Electrode oscillator current source base current • 2 µA setting (EXTCHRG = 0) • 32 µA setting (EXTCHRG = 15)	— —	2 36	3 50	µA	2, 7
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	9
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	10
MaxSens	Maximum sensitivity	0.008	1.46	—	fF/count	11
Res	Resolution	—	—	16	bits	
T _{Con20}	Response time @ 20 pF	8	15	25	µs	12
I _{TSI_RUN}	Current added in run mode	—	55	—	µA	
I _{TSI_LP}	Low power mode current adder	—	1.3	2.5	µA	13

- The TSI module is functional with capacitance values outside this range. However, optimal performance is not guaranteed.
- Fixed external capacitance of 20 pF.
- REFCHRG = 2, EXTCHRG=0.
- REFCHRG = 0, EXTCHRG = 10.
- V_{DD} = 3.0 V.
- The programmable current source value is generated by multiplying the SCANC[REFCHRG] value and the base current.
- The programmable current source value is generated by multiplying the SCANC[EXTCHRG] value and the base current.
- Measured with a 5 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 8; I_{ext} = 16.
- Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 2; I_{ext} = 16.
- Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 16, NSCN = 3; I_{ext} = 16.
- Sensitivity defines the minimum capacitance change when a single count from the TSI module changes. Sensitivity depends on the configuration used. The documented values are provided as examples calculated for a specific configuration of operating conditions using the following equation: $(C_{ref} * I_{ext}) / (I_{ref} * PS * NSCN)$

The typical value is calculated with the following configuration:

$$I_{ext} = 6 \mu A \text{ (EXTCHRG = 2), PS = 128, NSCN = 2, } I_{ref} = 16 \mu A \text{ (REFCHRG = 7), } C_{ref} = 1.0 \text{ pF}$$

The minimum value is calculated with the following configuration:

$$I_{ext} = 2 \mu A \text{ (EXTCHRG = 0), PS = 128, NSCN = 32, } I_{ref} = 32 \mu A \text{ (REFCHRG = 15), } C_{ref} = 0.5 \text{ pF}$$

The highest possible sensitivity is the minimum value because it represents the smallest possible capacitance that can be measured by a single count.

- Time to do one complete measurement of the electrode. Sensitivity resolution of 0.0133 pF, PS = 0, NSCN = 0, 1 electrode, EXTCHRG = 7.
- REFCHRG=0, EXTCHRG=4, PS=7, NSCN=0F, LPSCNITV=F, LPO is selected (1 kHz), and fixed external capacitance of 20 pF. Data is captured with an average of 7 periods window.

32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
14	PTA2	JTAG_TDO/ TRACE_SWO/ EZP_DO	TSIO_CH3	PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
15	PTA3	JTAG_TMS/ SWD_DIO	TSIO_CH4	PTA3	UART0_RTS_b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
16	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b	TSIO_CH5	PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
17	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0				
18	PTA19	XTAL0	XTAL0	PTA19		FTM1_FLT0	FTM_CLKIN1		LPTMR0_ALT1		
19	RESET_b	RESET_b	RESET_b								
20	PTB0/ LLWU_P5	ADC0_SE8/ TSIO_CH0	ADC0_SE8/ TSIO_CH0	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_ PHA		
21	PTB1	ADC0_SE9/ TSIO_CH6	ADC0_SE9/ TSIO_CH6	PTB1	I2C0_SDA	FTM1_CH1			FTM1_QD_ PHB		
22	PTC1/ LLWU_P6	ADC0_SE15/ TSIO_CH14	ADC0_SE15/ TSIO_CH14	PTC1/ LLWU_P6	SPI0_PCS3	UART1_RTS_b	FTM0_CH0		I2S0_TXD0		
23	PTC2	ADC0_SE4b/ CMP1_IN0/ TSIO_CH15	ADC0_SE4b/ CMP1_IN0/ TSIO_CH15	PTC2	SPI0_PCS2	UART1_CTS_b	FTM0_CH1		I2S0_TX_FS		
24	PTC3/ LLWU_P7	CMP1_IN1	CMP1_IN1	PTC3/ LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2		I2S0_TX_BCLK		
25	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	FTM0_CH3		CMP1_OUT		
26	PTC5/ LLWU_P9	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ALT2	I2S0_RXD0		CMP0_OUT		
27	PTC6/ LLWU_P10	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_SOUT	PDB0_EXTRG	I2S0_RX_BCLK		I2S0_MCLK		
28	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_SIN	USB_SOF_ OUT	I2S0_RX_FS				
29	PTD4/ LLWU_P14	DISABLED		PTD4/ LLWU_P14	SPI0_PCS1	UART0_RTS_b	FTM0_CH4		EWM_IN		
30	PTD5	ADC0_SE6b	ADC0_SE6b	PTD5	SPI0_PCS2	UART0_CTS_ b/ UART0_COL_b	FTM0_CH5		EWM_OUT_b		
31	PTD6/ LLWU_P15	ADC0_SE7b	ADC0_SE7b	PTD6/ LLWU_P15	SPI0_PCS3	UART0_RX	FTM0_CH6		FTM0_FLT0		
32	PTD7	DISABLED		PTD7	CMT_IRO	UART0_TX	FTM0_CH7		FTM0_FLT1		

8.2 K20 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

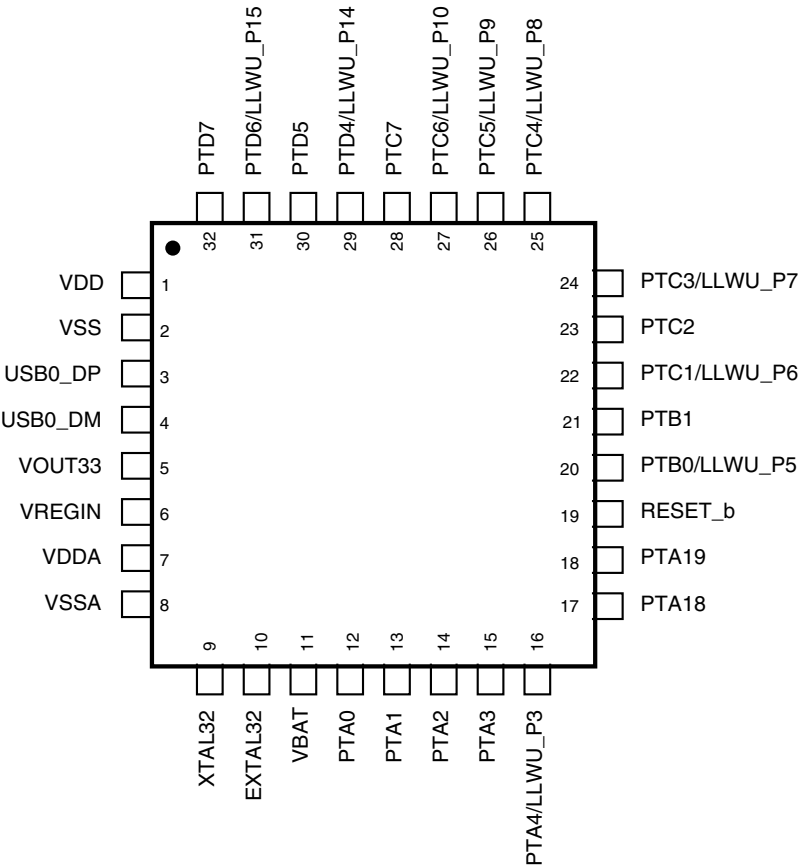


Figure 23. K20 32 QFN Pinout Diagram

9 Revision History

The following table provides a revision history for this document.

Table 37. Revision History

Rev. No.	Date	Substantial Changes
2	2/2012	Initial public release
3	4/2012	• Replaced TBDs throughout. • Updated "Power mode transition operating behaviors" table. • Updated "Power consumption operating behaviors" table. • For "Diagram: Typical IDD_RUN operating behavior" section, added "VLPR mode supply current vs. core frequency" figure. • Updated "EMC radiated emissions operating behaviors" section. • Updated "Thermal operating requirements" section. • Updated "MCG specifications" table. • Updated "VREF full-range operating behaviors" table. • Updated "I2S/SAI Switching Specifications" section. • Updated "TSI electrical specifications" table.

Table continues on the next page...